

# CDx4HC164、CDx4HCT164 ハイスピード CMOS ロジック、8 ビット、シリアル入力、パラレル出力、シフト・レジスタ

## 1 特長

- バッファ付き入力
- 非同期リセット
- $f_{MAX} = 60\text{MHz}$  (標準値、 $V_{CC} = 5\text{V}$ 、 $C_L = 15\text{pF}$ 、 $T_A = 25^\circ\text{C}$ )
- ファンアウト (全温度範囲にわたって)
  - 標準出力: 10 個の LSTTL 負荷
  - バス・ドライバ出力: 15 個の LSTTL 負荷
- 広い動作電圧範囲:  $-55^\circ\text{C} \sim 125^\circ\text{C}$
- 平衡な伝搬遅延と遷移時間
- LSTTL ロジック IC に比べて消費電力を大幅削減
- HC タイプ
  - $2\text{V} \sim 6\text{V}$  で動作
  - 優れたノイズ耐性:  $V_{CC}$  の  $N_{IL} = 30\%$ 、 $N_{IH} = 30\%$  ( $V_{CC} = 5\text{V}$  時)
- HCT タイプ
  - $4.5\text{V} \sim 5.5\text{V}$  で動作
  - LSTTL 入力ロジックと直接互換、 $V_{IL} = 0.8\text{V}$  (最大値)、 $V_{IH} = 2\text{V}$  (最小値)
  - CMOS 入力互換、 $V_{OL}$ 、 $V_{OH}$  で  $I_L \leq 1\mu\text{A}$

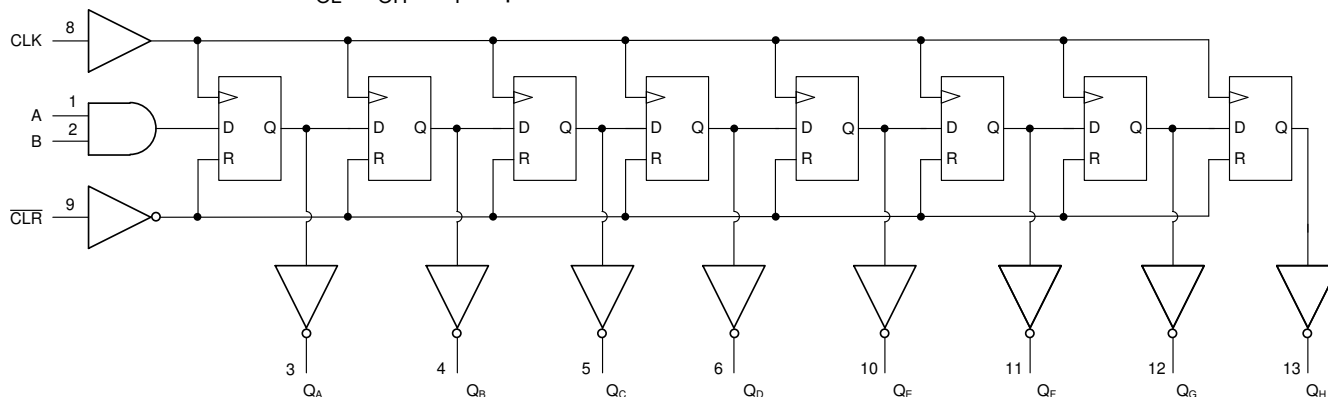
## 2 概要

HC164 および HCT164 は、非同期リセット搭載 8 ビット・シリアル入力パラレル出力シフト・レジスタです。データはクロック (CLK) の正のエッジでシフトされます。リセット (CLR) ピンが LOW になると、シフト・レジスタがリセットされ、入力の条件にかかわらずすべての出力が LOW 状態になります。2 つのシリアル・データ入力 (A と B) があり、どちらもデータ・イネーブル制御として使用できます。

### デバイス情報

部品番号	パッケージ <sup>(1)</sup>	本体サイズ (公称)
CD74HC164M	SOIC (14)	8.65mm × 3.90mm
CD74HCT164M	SOIC (14)	8.65mm × 3.90mm
CD74HC164E	PDIP (14)	19.31mm × 6.35mm
CD74HCT164E	PDIP (14)	19.31mm × 6.35mm
CD54HC164F	CDIP (14)	19.55mm × 6.71mm

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



機能ブロック図



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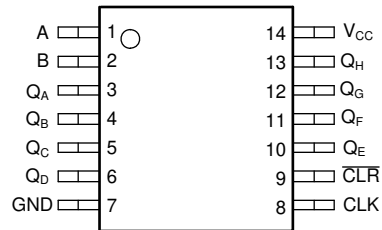
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### 3 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision C (August 2003) to Revision D (March 2022)	Page
• 最新のデータシート規格を反映するように、文書全体の表、図、相互参照の採番と書式設定を更新.....	1
• Updated naming conventions to reflect modern TI function. DS1 is now A; DS2 is now B; Q <sub>0</sub> is now Q <sub>A</sub> ; Q <sub>1</sub> is now Q <sub>B</sub> ; Q <sub>2</sub> is now Q <sub>C</sub> ; Q <sub>3</sub> is now Q <sub>D</sub> ; CP is now CLK; $\overline{MR}$ is now $\overline{CLR}$ ; Q <sub>4</sub> is now Q <sub>E</sub> ; Q <sub>5</sub> is now Q <sub>F</sub> ; Q <sub>6</sub> is now Q <sub>G</sub> ; Q <sub>7</sub> is now Q <sub>H</sub> .....	3

## 4 Pin Configuration and Functions



**J, D, and N Package  
14-Pin CDIP, SOIC, and PDIP  
Top View**

## 5 Specifications

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range	-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	(V <sub>I</sub> < 0 or V <sub>I</sub> > V <sub>CC</sub> )		±20 mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	(V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub> )		±20 mA
I <sub>O</sub>	Continuous output current	(V <sub>O</sub> = 0 to V <sub>CC</sub> )		±25 mA
	Continuous current through V <sub>CC</sub> or GND			±50 mA
T <sub>J</sub>	Junction temperature			150 °C
T <sub>stg</sub>	Storage temperature	-65	150	°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 5.2 Recommended Operating Conditions

		MIN	MAX	UNIT	
V <sub>CC</sub>	Supply voltage range	HC types	2	6	V
		HCT types	4.5	5.5	
V <sub>I</sub> , V <sub>O</sub>	Input or output voltage	0	V <sub>CC</sub>	V	
	Input rise and fall time	2 V	1000	ns	
		4.5 V	500		
		6 V	400		
T <sub>A</sub>	Temperature range	-55	125	°C	

### 5.3 Thermal Information

THERMAL METRIC		D (SOIC)	N (PDIP)	UNIT
		14 PINS	14 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance <sup>(1)</sup>	86	80	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC package thermal metrics](#) application report.

## 5.4 Electrical Characteristics

PARAMETER	TEST CONDITIONS <sup>(1)</sup>	V <sub>CC</sub> (V)	25°C			–40°C to 85°C		–55°C to 125°C		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>										
V <sub>IH</sub>	High level input voltage		2	1.5		1.5		1.5		V
			4.5	3.15		3.15		3.15		
			6	4.2		4.2		4.2		
V <sub>IL</sub>	Low level input voltage		2		0.5		0.5		0.5	V
			4.5		1.35		1.35		1.35	
			6		1.8		1.8		1.8	
V <sub>OH</sub>	High level output voltage	I <sub>OH</sub> = – 20 μA	2	1.9		1.9		1.9		V
		I <sub>OH</sub> = – 20 μA	4.5	4.4		4.4		4.4		
		I <sub>OH</sub> = – 20 μA	6	5.9		5.9		5.9		
	High level output voltage	I <sub>OH</sub> = – 4 mA	4.5	3.98		3.84		3.7		
		I <sub>OH</sub> = – 5.2 mA	6	5.48		5.34		5.2		
V <sub>OL</sub>	Low level output voltage	I <sub>OL</sub> = 20 μA	2		0.1		0.1		0.1	V
		I <sub>OL</sub> = 20 μA	4.5		0.1		0.1		0.1	
		I <sub>OL</sub> = 20 μA	6		0.1		0.1		0.1	
	Low level output voltage	I <sub>OL</sub> = 4 mA	4.5		0.26		0.33		0.4	
		I <sub>OL</sub> = 5.2 mA	6		0.26		0.33		0.4	
I <sub>I</sub>	Input leakage current		6		±0.1		±1		±1	μA
I <sub>CC</sub>	Supply current	V <sub>I</sub> = V <sub>CC</sub> or GND	6		8		80		160	μA
<b>HCT TYPES</b>										
V <sub>IH</sub>	High level input voltage		4.5 to 5.5	2		2		2		V
V <sub>IL</sub>	Low level input voltage		4.5 to 5.5		0.8		0.8		0.8	V
V <sub>OH</sub>	High level output voltage	I <sub>OH</sub> = – 20 μA	4.5	4.4		4.4		4.4		V
	High level output voltage	I <sub>OH</sub> = – 4 μA	4.5	3.98		3.84		3.7		
V <sub>OL</sub>	Low level output voltage	I <sub>OL</sub> = 20 μA	4.5		0.1		0.1		0.1	V
	Low level output voltage	I <sub>OL</sub> = 4 μA	4.5		0.26		0.33		0.4	
I <sub>I</sub>	Input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND	5.5		±0.1		±1		±1	μA
I <sub>CC</sub>	Supply current	V <sub>I</sub> = V <sub>CC</sub> or GND	5.5		8		80		160	μA
ΔI <sub>CC</sub> <sup>(2) (3)</sup>	Additional supply current per input pin	Date Shift-In (1,2)	4.5 to 5.5	100	108		135		147	μA
		CLR	4.5 to 5.5		324		405		441	μA
		CLK	4.5 to 5.5	100	252		315		343	μA

(1) V<sub>I</sub> = V<sub>IH</sub> or V<sub>IL</sub>, unless otherwise noted.

(2) This is the increase in supply current for each input that is at one of the specified TTL voltage levels, rather than 0 V or V<sub>CC</sub>.

(3) Inputs held at V<sub>CC</sub> – 2.1.

## 5.5 Prerequisite for Switching Characteristics

PARAMETER		V <sub>CC</sub> (V)	25°C		– 40°C to 85°C		– 55°C to 125°C		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>									
f <sub>MAX</sub>	Maximum clock frequency	2	6	5	4	MHz			
		4.5	30	24	20	MHz			
		6	35	28	24	MHz			
t <sub>W</sub>	CLR pulse width	2	60	75	90	ns			
		4.5	12	15	18	ns			
		6	10	13	15	ns			
t <sub>W</sub>	CLK pulse width	2	80	100	120	ns			
		4.5	16	20	24	ns			
		6	14	17	20	ns			
t <sub>SU</sub>	Set-up time	2	60	75	90	ns			
		4.5	12	15	18	ns			
		6	10	13	15	ns			
t <sub>H</sub>	Hold time	2	4	4	4	ns			
		4.5	4	4	4	ns			
		6	4	4	4	ns			
t <sub>REM</sub>	CLR to clock, Removal time	2	80	100	120	ns			
		4.5	16	20	24	ns			
		6	14	17	20	ns			
<b>HCT TYPES</b>									
f <sub>MAX</sub>	Maximum clock frequency	4.5	27	22	18	MHz			
t <sub>W</sub>	CLR pulse width	6	18	23	27	ns			
t <sub>W</sub>	CLK pulse width	4.5	18	23	27	ns			
t <sub>SU</sub>	Set-up time	6	12	15	18	ns			
t <sub>H</sub>	Hold time	4.5	4	4	4	ns			
t <sub>REM</sub>	CLR to clock, Removal time	6	16	20	24	ns			

## 5.6 Switching Characteristics

Input  $t_r$ ,  $t_f$  = 6ns.  $C_L$  = 50pF unless otherwise noted

PARAMETER		$V_{CC}$ (V)	25°C		- 40°C to 85°C	- 55°C to 125°C	UNIT
			TYP	MAX	MAX	MAX	
<b>HC TYPES</b>							
$t_{PLH}$ , $t_{PHL}$	CLK to Q	2		170	212	255	ns
		4.5	14 <sup>(3)</sup>	34	43	51	ns
		6		29	36	43	ns
$t_{PLH}$ , $t_{PHL}$	$\overline{CLR}$ to Q	2		140	175	210	ns
		4.5	11 <sup>(3)</sup>	28	35	42	ns
		6		24	30	36	ns
$t_{TLH}$ , $t_{THL}$	Output transition times	2		75		110	ns
		4.5		15		22	ns
		6		13		19	ns
$f_{MAX}$	Maximum clock frequency	5	60 <sup>(3)</sup>				ns
$C_{IN}$	Input capacitance			10	10	10	pF
$C_{PD}$	Power dissipation capacitance <sup>(1) (2)</sup>	5	47				pF
<b>HCT TYPES</b>							
$t_{PLH}$ , $t_{PHL}$	CLK to Q	4.5		36	45	54	ns
		5	15 <sup>(3)</sup>				
$t_{PLH}$ , $t_{PHL}$	$\overline{CLR}$ to Q	4.5		38	46	57	ns
		5	16 <sup>(3)</sup>				
$t_{TLH}$ , $t_{THL}$	Output Transition time	4.5		15	19	22	ns
$C_{IN}$	Input Capacitance						pF
$f_{MAX}$	Maximum clock frequency		54 <sup>(4)</sup>				MHz
$C_{PD}$	Power dissipation capacitance <sup>(1) (2)</sup>	5	49	10	10	10	pF

(1)  $C_{PD}$  is used to determine the dynamic power consumption, per device.

(2)  $P_D = V_{CC}^2 f_i + \sum (C_L V_{CC}^2 + f_o)$  where  $f_i$  = Input Frequency,  $f_o$  = Output Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

(3)  $C_L = 15\text{pF}$ .  $V_{CC} = 5$ .

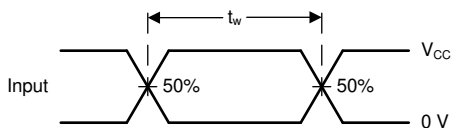
(4)  $C_L = 15\text{pF}$ .

## 6 Parameter Measurement Information

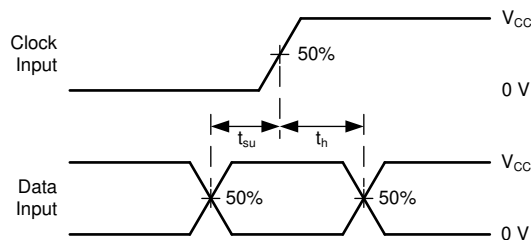
Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 1 \text{ MHz}$ ,  $Z_O = 50 \Omega$ ,  $t_t < 6 \text{ ns}$ .

For clock inputs,  $f_{\text{max}}$  is measured when the input duty cycle is 50%.

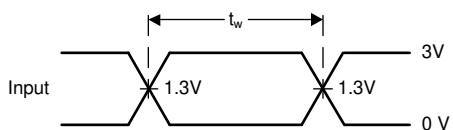
The outputs are measured one at a time with one input transition per measurement.



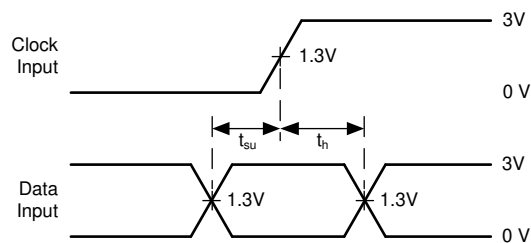
**Figure 6-1. Voltage Waveforms, Standard CMOS Inputs Pulse Duration**



**Figure 6-2. Voltage Waveforms, Standard CMOS Inputs Setup and Hold Times**



**Figure 6-3. Voltage Waveforms, TTL-Compatible CMOS Inputs Pulse Duration**



**Figure 6-4. Voltage Waveforms, TTL-Compatible CMOS Inputs Setup and Hold Times**

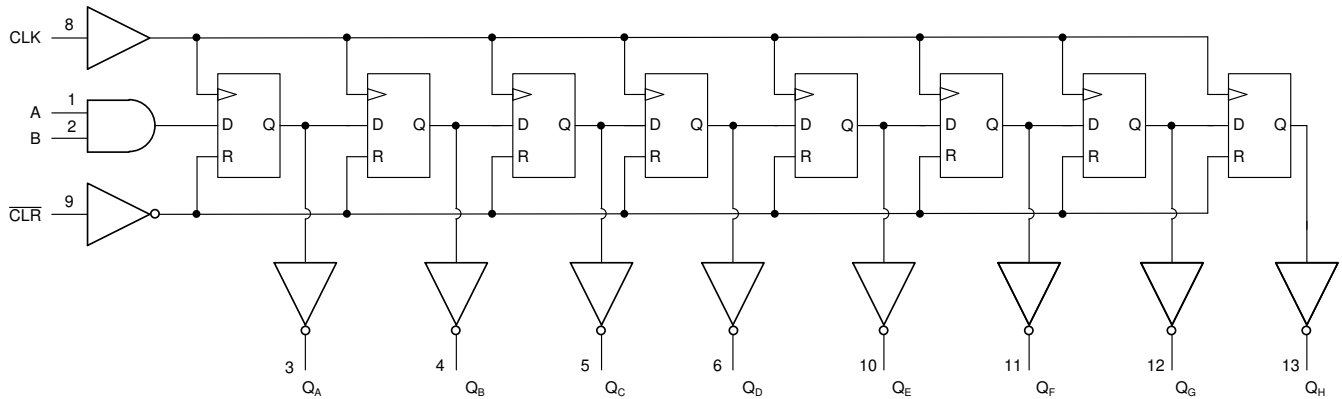


## 7 Detailed Description

### 7.1 Overview

The 'HC164 and 'HCT164 are 8-bit serial-in parallel-out shift registers with asynchronous reset. Data is shifted on the positive edge of Clock (CLK). A LOW on the Reset ( $\overline{\text{CLR}}$ ) pin resets the shift register and all outputs go to the LOW state regardless of the input conditions. Two Serial Data inputs (A and B) are provided, either one can be used as a Data Enable control.

### 7.2 Functional Block Diagram



7-1. Functional Block Diagram

### 7.3 Device Functional Modes

Truth Table<sup>(1)</sup>

OPERATING MODE	INPUTS				OUTPUTS	
	$\overline{\text{CLR}}$	CLK	A	B	QA	QB - QH
RESET (CLEAR)	L	X	X	X	L	L - L
Shift	H	↑	l	l	L	QA - QF
	H	↑	l	h	L	QA - QF
	H	↑	h	l	L	QA - QF
	H	↑	h	h	H	QA - QF

- (1) H = High voltage level.  
h = High voltage level one set-up time prior to the low-to-high clock transition.  
l = Low voltage level one set-up time prior to the low-to-high clock transition.  
L = Low voltage level.  
X = Don't care.  
↑ = Transition from low to high level.  
q<sub>n</sub> = Lower case letters indicate the state of the reference input clock transition.

## 8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu\text{F}$  capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu\text{F}$  and 1- $\mu\text{F}$  capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

## 9 Layout

### 9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.

## 10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 10.1 Documentation Support

#### 10.1.1 Related Documentation

#### 10.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 10.3 サポート・リソース

[TI E2E™ サポート・フォーラム](#)は、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

リンクされているコンテンツは、該当する貢献者により、現状のまま提供されるものです。これらは TI の仕様を構成するものではなく、必ずしも TI の見解を反映したものではありません。TI の[使用条件](#)を参照してください。

#### 10.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

#### 10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 10.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8970401CA	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8970401CA CD54HCT164F3A	<a href="#">Samples</a>
CD54HC164F	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HC164F	<a href="#">Samples</a>
CD54HC164F3A	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8416201CA CD54HC164F3A	<a href="#">Samples</a>
CD54HCT164F3A	ACTIVE	CDIP	J	14	25	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8970401CA CD54HCT164F3A	<a href="#">Samples</a>
CD74HC164E	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC164E	<a href="#">Samples</a>
CD74HC164M96	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC164M	<a href="#">Samples</a>
CD74HC164M96G4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC164M	<a href="#">Samples</a>
CD74HCT164E	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT164E	<a href="#">Samples</a>
CD74HCT164M96	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-55 to 125	(HCT164, HCT164M)	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**OTHER QUALIFIED VERSIONS OF CD54HC164, CD54HCT164, CD74HC164, CD74HCT164 :**

- Catalog : [CD74HC164](#), [CD74HCT164](#)
- Military : [CD54HC164](#), [CD54HCT164](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Military - QML certified for Military and Defense Applications

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC164M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD74HCT164M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CD74HCT164M96	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
CD74HCT164M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

## TAPE AND REEL BOX DIMENSIONS



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CD74HC164M96	SOIC	D	14	2500	356.0	356.0	35.0
CD74HCT164M96	SOIC	D	14	2500	356.0	356.0	35.0
CD74HCT164M96	SOIC	D	14	2500	366.0	364.0	50.0
CD74HCT164M96	SOIC	D	14	2500	356.0	356.0	35.0

**TUBE**


\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
CD74HC164E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HC164E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT164E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HCT164E	N	PDIP	14	25	506	13.97	11230	4.32



J 14

**GENERIC PACKAGE VIEW**  
**CDIP - 5.08 mm max height**  
CERAMIC DUAL IN LINE PACKAGE



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

4040083-5/G



# EXAMPLE BOARD LAYOUT

J0014A

CDIP - 5.08 mm max height

CERAMIC DUAL IN LINE PACKAGE



LAND PATTERN EXAMPLE  
NON-SOLDER MASK DEFINED  
SCALE: 5X



4214771/A 05/2017



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



4040049/E 12/2002

- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - $\triangle C$  Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
  - $\triangle D$  The 20 pin end lead shoulder width is a vendor option, either half or full width.

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郵送先住所 : Texas Instruments, Post Office Box 655303, Dallas, Texas 75265  
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